

Transistors

2.5V Drive Nch MOS FET

RJK005N03

●Structure

Silicon N-channel MOS FET

●Features

- 1) Low On-resistance.
- 2) Low voltage drive (2.5V drive).

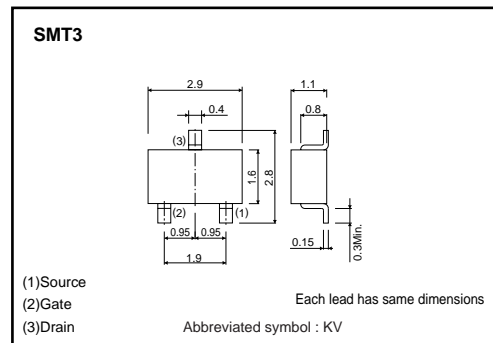
●Applications

Switching

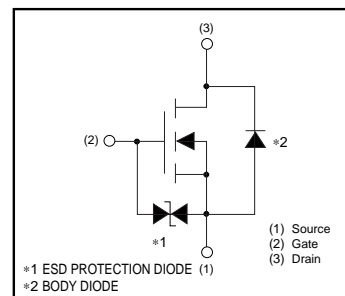
●Packaging specifications and hFE

Type	Package	Taping
	Code	T146
	Basic ordering unit (pieces)	3000
RJK005N03		○

●External dimensions (Unit : mm)



●Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DSS}	30	V
Gate-source voltage	V_{GSS}	± 12	V
Drain current	Continuous	I_D	± 500 mA
	Pulsed	I_{DP} *1	± 2.0 A
Source current (Body Diode)	Continuous	I_S	200 mA
	Pulsed	I_{SP} *1	800 mA
Total power dissipation	P_D *2	200	mW
Channel temperature	T_{ch}	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

*2 Each terminal mounted on a recommended land

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th(ch-a)}$ *	625	°C/W

* Each terminal mounted on a recommended land

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	$V_{GS}=\pm 12V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR) DSS}$	30	–	–	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	–	–	1	μA	$V_{DS}=30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	0.8	–	1.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	400	580	mΩ	$I_D=500mA, V_{GS}=4.5V$
		–	420	600	mΩ	$I_D=500mA, V_{GS}=4V$
		–	650	940	mΩ	$I_D=500mA, V_{GS}=2.5V$
Forward transfer admittance	$ Y_{fs} $ *	0.5	–	–	S	$V_{DS}=10V, I_D=500mA$
Input capacitance	C_{iss}	–	60	–	pF	$V_{DS}=10V$
Output capacitance	C_{oss}	–	24	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	–	12	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	9	–	ns	$V_{DD}\doteq 15V$
Rise time	t_r *	–	11	–	ns	$I_D=250mA$
Turn-off delay time	$t_{d(off)}$ *	–	16	–	ns	$V_{GS}=4V$
Fall time	t_f *	–	31	–	ns	$R_L=60\Omega$
Total gate charge	Q_g *	–	2.0	4.0	nC	$V_{DD}\doteq 24V$
Gate-source charge	Q_{gs} *	–	0.6	–	nC	$V_{GS}=4V$
Gate-drain charge	Q_{gd} *	–	0.7	–	nC	$I_D=500mA$

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD} *	–	–	1.2	V	$I_S=500mA, V_{GS}=0V$

*Pulsed

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